VHF POWER MOSFET
N-Channel Enhancement Mode

DESCRIPTION:

The **ASI BLF246** is a vertical D-MOS transistor designed for large signal amplifier applications in the VHF frequency range.

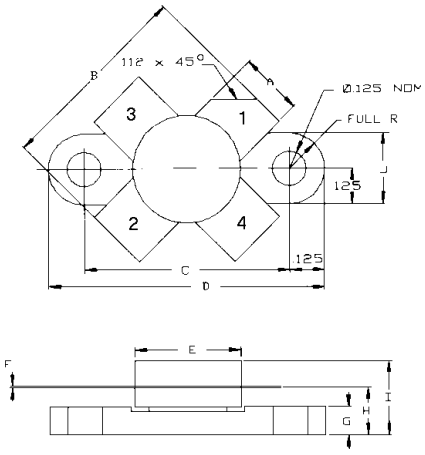
FEATURES INCLUDE:

- P_G = 13 dB Typical at 175 MHz
- **30:1** Load VSWR Capability
- ***Omnigold***™ metalization system

MAXIMUM RATINGS

I_D	13 A
V_{DS}	65 V
V_{GS}	± 20 V
P_{DISS}	130 W @ T_C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.35 °C/W

PACKAGE STYLE .380 4L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.785/19,94	
C	.720/18,29	.730/18,54
D	.970/24,64	.980/24,89
E		.385/9,78
F	.004/0,10	.006/0,15
G	.085/2,16	.105/2,67
H	.160/4,06	.180/4,57
I		.280/7,11
J	.240/6,10	.255/6,48

1 = DRAIN 2 = GATE 3&4 = SOURCE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_D = 50 mA			65			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				2.5	mA
I_{GSS}	V_{DS} = 0 V	V_{GS} = ±20 V				1.0	µA
$V_{GS(th)}$	V_{DS} = 10 V	I_D = 50 mA		2.0		4.5	V
g_{fs}	V_{DS} = 10 V	I_D = 2.5 A		3.0	4.2		S
$R_{DS(on)}$	V_{GS} = 10 V	I_D = 5.0 A			0.2	0.3	Ω
C_{is} C_{os} C_{rs}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		225 180 25		pF
P_G η_D	V_{DS} = 28 V I_{DQ} = 0.1 A	P_{out} = 80 W	f = 108 MHz	16 55			dB %

Specifications are subject to change without notice.